(19) World Intellectual Property Organization

International Bureau





(43) International Publication Date 31 July 2003 (31.07.2003)

PCT

(10) International Publication Number WO 2003/063171 A3

(51) International Patent Classification⁷: G11C 16/26,

(21) International Application Number:

PCT/US2002/040204

(22) International Filing Date:

16 December 2002 (16.12.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

10/052,924 18 January 2002 (18.01.2002) US

(71) Applicant: SANDISK CORPORATION [US/US]; 140 Caspian Court, Sunnyvale, CA 94089 (US).

(72) Inventors: MOKHLESI, Nima; 14285 Selinda Way, Los Gatos, CA 95032 (US). GUTERMAN, Daniel, C.; 305 Jacaranda Drive, Fremont, CA 94539 (US). GONGWER, Geoffrey, S.; 5328 Beechwood Lane, Los Altos, CA 94024 (US).

(74) Agents: CLEVELAND, Michael, G. et al.; Parsons Hsue & de Runtz LLP, 655 Montgomery Street, Suite 1800, San Francisco, CA 94111 (US).

(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

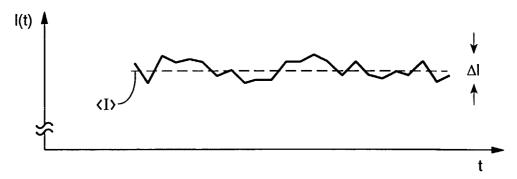
— with international search report

(88) Date of publication of the international search report:

31 December 2003

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: NOISE REDUCTION TECHNIQUE FOR TRANSISTORS AND SMALL DEVICES UTILIZING AN EPISODIC AGITATION



(57) Abstract: The present invention presents methods for reducing the amount of noise inherent in the reading of a non-volatile storage device by applying an episodic agitation (e.g. a time varying voltage) to some terminal(s) of the cell as part of the reading process. Various aspects of the present invention also extend to devices beyond non-volatile memories. According to one aspect of the present invention, in addition to the normal voltage levels applied to the cell as part of the reading process, a time varying voltage is applied to the cell. A set of exemplary embodiments apply a single or multiple set of alternating voltages to one or more terminals of a floating gate memory cell just prior to or during the signal integration time of a read process. In other embodiments, other reproducible external or internal agitations which are repeatable, and whose average effect (from one integration time to the next integration time) remains sufficiently constant so as to have a net noise reduction effect is applicable.



INTERNATIONAL SEARCH REPORT

Internation No PCT/US 02/40204

A. CLASSIFICATION OF SUBJECT MATTER IPC 7 G11C16/26 G11C11/56

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols) $IPC\ 7\ G11C$

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal

C. DOCUM	ENTS CONSIDERED TO BE RELEVANT				
Category °	Citation of document, with indication, where appropriate, of the r	Relevant to claim No.			
X	WO 01 27931 A (APLUS FLASH TECHN 19 April 2001 (2001-04-19)	1-7,9, 15,16, 29-32, 34,35, 39,40, 53-57			
А	page 7, line 18 -page 8, line 14	8,10-14, 17-28, 33, 36-38, 41-52, 58-70			
Α	WO 95 19047 A (HYUNDAI ELECTRON) 13 July 1995 (1995-07-13) page 11, line 8-15; figures 2A-0	 95 19047 A (HYUNDAI ELECTRONICS IND) 3 July 1995 (1995-07-13) age 11, line 8-15; figures 2A-C -/			
	her documents are listed in the continuation of box C.	Patent family members are listed	ernational filing date		
consid	ent defining the general state of the art which is not dered to be of particular relevance document but published on or after the international date	or priority date and not in conflict with cited to understand the principle or th invention "X" document of particular relevance; the cannot be considered novel or canno	eory underlying the claimed invention		
"L" docume which citatio "O" docume other	ent which may throw doubts on priority claim(s) or is cited to establish the publication date of another on or other special reason (as specified) nent referring to an oral disclosure, use, exhibition or means	"Y" document of particular relevance; the cannot be considered to involve an in document is combined with one or m ments, such combination being obvic in the art.	ocument is taken alone claimed invention nventive step when the ore other such docu-		
later t	ent published prior to the international filing date but han the priority date claimed	*&* document member of the same patent			
	actual completion of the international search	Date of mailing of the international se	акы тероп		
3	30 September 2003	10/10/2003			
Name and	mailing address of the ISA European Patent Office, P.B. 5818 Patentlaan 2 NL – 2280 HV Rijswijk Tel. (+31-70) 340-2040, Tx. 31 651 epo nl, Fax: (+31-70) 340-3016	Authorized officer Lindquist, J			

INTERNATIONAL SEARCH REPORT

Int phal Application No
PCT/US 02/40204

(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT	
ategory of Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
MA Y ET AL: "A dual-bit split-gate EEPROM (DSG) cell in contactless array for single-Vcc high density flash memories" ELECTRON DEVICES MEETING, 1994. TECHNICAL DIGEST., INTERNATIONAL SAN FRANCISCO, CA, USA 11-14 DEC. 1994, NEW YORK, NY, USA, IEEE, 11 December 1994 (1994-12-11), pages 57-60, XP010131952 ISBN: 0-7803-2111-1 page 3.5.2, left-hand column, line 30 -right-hand column, line 3	1–70

INTERNATIONAL SEARCH REPORT

Information on patent family members

Inte nal Application No
PCT/US 02/40204

Patent document cited in search report		Publication date		Patent family member(s)	Publication date
WO 0127931	А	19-04-2001	AU WO US	8000200 A 0127931 A1 6275417 B1	23-04-2001 19-04-2001 14-08-2001
WO 9519047	A	13-07-1995	US US US WO AT DE DK EP JP	5278439 A 5364806 A 5414693 A 9519047 A1 238609 T 69432568 D1 740854 T3 0740854 A1 9507341 T	11-01-1994 15-11-1994 09-05-1995 13-07-1995 15-05-2003 28-05-2003 18-08-2003 06-11-1996 22-07-1997